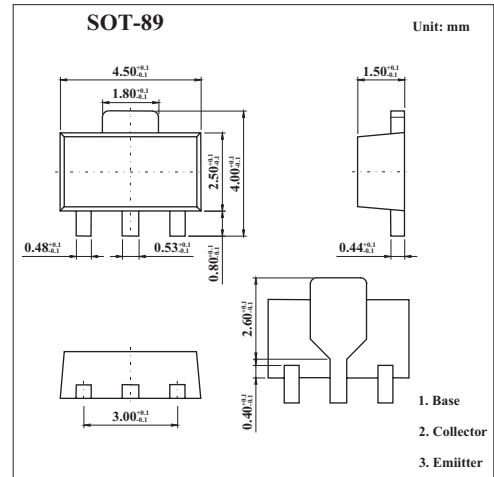


BCX69

■ Features

- For general AF applications.
- High collector current.
- High current gain.
- Low collector-emitter saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	20	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	1	A
Peak collector current	I _{CM}	2	A
Base current	I _B	100	mA
Peak base current	I _{BM}	200	mA
Total power dissipation	P _{tot}	1	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C
Junction - soldering point	R _{thJS}	≤20	K/W

BCX69

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Collector-emitter breakdown voltage	V(BR)CEO	Ic = 30 mA, Ib = 0	20			V	
Collector-base breakdown voltage	V(BR)CBO	Ic = 10 μA, Ib = 0	25			V	
Emitter-base breakdown voltage	V(BR)EBO	Ie = 1 μA, Ic = 0	5			V	
Collector cutoff current	IcBO	Vcb = 25 V, Ie = 0			100	nA	
		Vcb = 25 V, Ie = 0, TA = 150 °C			100	μA	
DC current gain *	hFE	Ic = 5 mA, Vce = 10 V	50				
DC current gain *	hFE	Ic = 500 mA, Vce = 1 V	BCX69	85		375	
			BCX69-10	85	100	160	
			BCX69-16	100	160	250	
			BCX69-25	160	250	375	
DC current gain *	hFE	Ic = 1A, Vce = 1V	60				
Collector-emitter saturation voltage *	VCE(sat)	Ic = 1 A, Ib = 100 mA			0.5	V	
Base-emitter voltage *	VBE(ON)	Ic = 5 mA, Vce = 10 V		0.6			
		Ic = 1 A, Vce = 1 V			1		
Transition frequency	fr	Ic = 100 mA, Vce = 5 V, f = 20 MHz		100		MHz	

* Pulse test: t ≤ 300μs, D = 2%.

■ hFE Classification

TYPE	BCX69	BCX69-10	BCX69-16	BCX69-25
Marking	CE	CF	CG	CH